

# Microelectronics Circuit Analysis and Design

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## Chapter 3

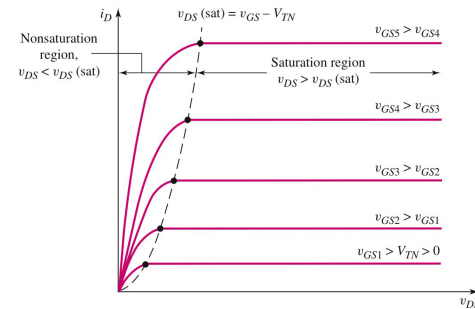
### MOSFET DC ANALYSIS

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Chapter 3-1

## Family of $i_D$ Versus $v_{DS}$ Curves: Enhancement-Mode nMOSFET



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## Summary of I-V Relationships

Region	NMOS	PMOS
Nonsaturation	$v_{DS} < v_{DS}(\text{sat})$ $i_D = K_n [2(v_{GS} - V_{TN})v_{DS} - v_{DS}^2]$	$v_{SD} < v_{SD}(\text{sat})$ $i_D = K_p [2(v_{SG} + V_{TP})v_{SD} - v_{SD}^2]$
Saturation	$v_{DS} > v_{DS}(\text{sat})$ $i_D = K_n [v_{GS} - V_{TN}]^2$	$v_{SD} > v_{SD}(\text{sat})$ $i_D = K_p [v_{SG} + V_{TP}]^2$
Transition Pt.	$v_{DS}(\text{sat}) = v_{GS} - V_{TN}$	$v_{SD}(\text{sat}) = v_{SG} + V_{TP}$
Enhancement Mode	$V_{TN} > 0V$	$V_{TP} < 0V$
Depletion Mode	$V_{TN} < 0V$	$V_{TP} > 0V$

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## Conduction Parameters

□ NMOSFET

$$K_n = \frac{W\mu_n C_{ox}}{2L} = k_n' \frac{W}{2L}$$

□ PMOSFET

$$K_p = \frac{W\mu_p C_{ox}}{2L} = k_p' \frac{W}{2L}$$

where:

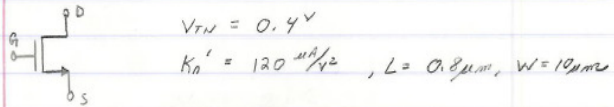
$$C_{ox} = \epsilon_o / t_{ox}$$

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Ex. 1 Given: N MOS Enhancement Type MOSFET



FIND:  $I_D$  {for table of  $V_{DS}$  &  $V_{GS}$ }

$$① K_n = \frac{K_n'}{2} \cdot \frac{W}{L} = \left(\frac{120}{2}\right) \left(\frac{10}{0.8}\right) = 0.75 \text{ mA/V}$$

$$② I_D = K_n [2(V_{GS} - V_{TH})V_{DS} - V_{DS}^2]$$

$$③ I_D = K_n [(V_{GS} - V_{TH})^2]$$

$$④ V_{DS(SAT)} = V_{GS} - V_{TH}$$

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Ex. 1 (cont.)

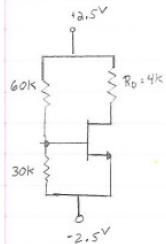
	$V_{DS}$	$V_{GS}$	$V_{DS(SAT)}$	$I_D$
(i)	0.1	0	-0.4	0 $V_{GS} < V_{TH}$ cut-off
(ii)	0.1	1	0.6	$0.75(2[1-0.4]0.1 - (0.1)^2) = 82.5 \mu A$
(iii)	0.1	2	1.6	$0.75(2[2-0.4]0.1 - (0.1)^2) = 232 \mu A$
(iv)	0.1	3	2.6	$0.75(2[3-0.4]0.1 - (0.1)^2) = 393 \mu A$
(v)	4	0	-0.4	0
(vi)	4	1	0.6	$0.75(1-0.4)^2 = 270 \mu A$
(vii)	4	2	1.6	$0.75(2-0.4)^2 = 1.92 \text{ mA}$
(viii)	4	3	2.6	$0.75(3-0.4)^2 = 5.07 \text{ mA}$

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Ex. 2



$$V_{TH} = 0.6V$$

$$K_n = 0.5 \text{ mA/V}^2$$

FIND:  $V_{GS}$ ,  $I_D$ ,  $V_{DS}$

$$① V_G = \left(\frac{30k}{30k+60k}\right) 5 - 2.5V = -0.833V$$

$$② V_S = -2.5V$$

$$③ V_{GS} = -0.833 - (-2.5) = 1.67V$$

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EX. 2

④ Assume SAT. Region.

$$I_D = K_n (V_{GS} - V_{TH})^2$$

$$= 0.5 \text{ mA/V}^2 (1.67 - 0.6)^2$$

$$= 0.57 \text{ mA}$$

$$5. -2.5 + I_D 4k + V_{DS} - 2.5 = 0$$

$$V_{DS} = 5 - (0.57)4$$

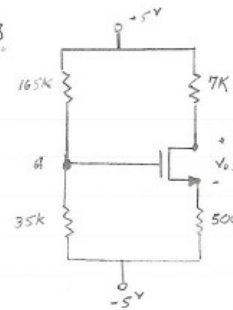
$$= 2.72V$$

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Ex. 3



Given:

$$V_{TN} = 0.8V$$

$$K_N = 1mA/V^2$$

Find:  $I_D$ ,  $V_{DS}$

$$① V_G = \left( \frac{35}{35+165} \right) 10 - 5 = -3.25V$$

$$② I_D = K_N (V_{GS} - V_{TN})^2$$

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Ex. 3 (Cont.)

$$② I_D = K_N (V_{GS} - V_{TN})^2$$

$$\frac{V_S - (-5)}{R_S} = K_N (V_G - V_S - V_{TN})^2$$

$$V_S + 5 = (500)(1mA/V^2)(-3.25 - V_S - 0.8)^2$$

$$2V_S + 10 = (-V_S - 4.05)^2$$

$$V_S^2 + 6.1V_S + 6.4 = 0$$

$$V_S = -4.75V \text{ or } -1.35V$$

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Ex. 3 (Cont.)

$$③ V_{GS} = -3.25 - (-4.75) = 1.5V > V_{TN} \checkmark$$

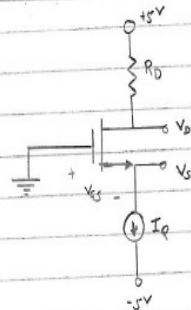
$$④ I_D = \frac{V_S + 5}{R_S} = \frac{-4.75 + 5}{500} = 0.5mA$$

$$⑤ -5V + I_D(7k + 500) + V_{DS} - 5V = 0$$

$$V_{DS} = 10 - (0.5)(7.5) = 6.25V$$

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Ex. 4 MOSFET BIASED w/ Constant Current Source



Given:

$$V_{TN} = 0.8V$$

$$K_N' = 80\mu A/V^2$$

$$W/L = 3$$

$$I_Q = 250\mu A, V_D = 2.5V$$

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## Ex.. 4 cont.

$$I_D = \frac{K_n'}{2} \cdot \frac{W}{L} (V_{GS} - V_{TN})^2$$

$$250 \mu A = \left( \frac{80 \mu A/V^2}{2} \right) (3) (V_{GS} - 0.8)^2 \Rightarrow V_{GS} = 2.24 V$$

$$V_S = -V_{GS} = -2.24 V$$

$$I_D = \frac{5 - V_D}{R_D} \Rightarrow \text{for } V_D = 2.5 \Rightarrow R_D = \frac{5 - 2.5}{0.25} = 10 K\Omega$$

$$V_{DS} = V_D - V_S = 2.5 - (-2.24) = 4.74 V$$

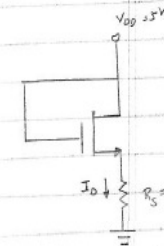
Since  $V_{DS} > V_{DS(sat)} = 2.24 - 0.8 = 1.44 V$ ,  $\therefore$  in SAT. REGION

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## Example: 5



$$K_n = 0.05 \text{ mA/V}^2$$

$$V_{TN} = 0.8 V$$

Assume SAT; then

$$I_D = K_n (V_{GS} - V_{TN})^2$$

$$V_{DS} = V_{GS} = 5 - I_D R_S$$

Subst: we get  $V_{GS} = 5 - K_n R_S (V_{GS} - V_{TN})^2 = 5 - (0.05)(10)(V_{GS} - 0.8)^2$

$$0.5 V_{GS}^2 + 0.2 V_{GS} - 4.68 = 0$$

$$V_{GS} = -3.27 V \text{ or } 2.87 V$$

$V_{GS}$  must  $> V_{TN}$   $\therefore V_{GS} = 2.87 V$ ,  $I_D = K_n (2.87 - 0.8)^2 = 0.213 \text{ mA}$

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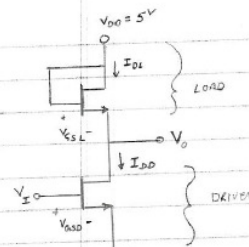
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## Ex. 6

Let:  $V_{TN0} = V_{TNL} = 1 V$

$$K_{ND} = 50 \mu A/V^2$$

$$K_{NL} = 10 \mu A/V^2$$



Find  $V_O$  for  $V_I = 5 V$

Assume  $M_D$  is in NON-SAT REGION &  $M_L$  is SAT so before

$$I_{DD} = I_{DL}$$

$$K_{ND} [2(V_{GS0} - V_{TN0})V_{DS0} - V_{DS0}^2] = K_{NL} [V_{GS0} - V_{TN0}]^2$$

Since:  $V_{GS0} = V_I$ ,  $V_{DS0} = V_O$ ,  $V_{GS0} = V_{DS0} = V_{DD} - V_O$

$$\text{then } K_{ND} [2(V_I - V_{TN0})V_O - V_O^2] = K_{NL} [V_{DD} - V_O - V_{TNL}]^2$$

$$\text{So } 50 [2(5 - 1)V_O - V_O^2] = 10 [5 - V_O - 1]^2$$

$$3V_O^2 - 24V_O + 8 = 0$$

$$V_O = 7.65 V \text{ or } 0.349 V$$

Note:  $V_{DS0} = V_O < V_{ISAT} = V_{GS0} - V_{TN0} = 5 - 1 = 4 V$   $\therefore$  NON-SAT. DRIVER

ALSO  $I_D = K_{NL} (V_{GS0} - V_{TNL})^2 = K_{NL} (V_{DD} - V_O - V_{TNL})^2$   
 $= 10 (5 - 0.349 - 1)^2 = 133 \mu A$

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